查询XP01215供应商 Composite Transistors 

# ,24小时加急 **Pamasonic**

# XP01215 (XP1215)

# Silicon NPN epitaxial planer transistor

For switching/digital circuits

#### Features

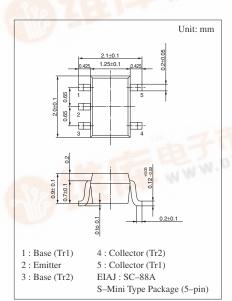
- Two elements incorporated into one package. (Emitter-coupled transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half.

#### Basic Part Number of Element

• UNR1215(UN1215)  $\times$  2 elements

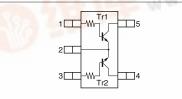
Aboolato Maximum Hatingo (11–25 C)								
Parameter		Symbol	Ratings	Unit				
Rating of element	Collector to base voltage	V <sub>CBO</sub>	50	V				
	Collector to emitter voltage	V <sub>CEO</sub>	50	V				
	Collector current	$I_C$	100	mA				
Overall	Total power dissipation	P <sub>T</sub>	150	mW				
	Junction temperature	Tj	150	°C				
	Storage temperature	T <sub>stg</sub>	-55 to +150	°C				

# Absolute Maximum Ratings (Ta=25°C)



#### Marking Symbol: 9M

#### Internal Connection

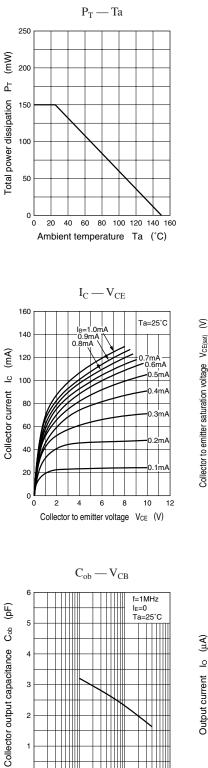


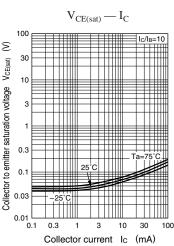
#### Electrical Characteristics (Ta=25°C)

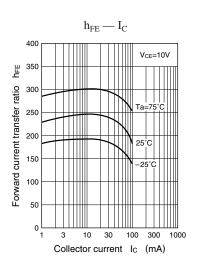
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to base voltage	V <sub>CBO</sub>	$I_{\rm C} = 10 \mu A, I_{\rm E} = 0$	50		1.11	V
Collector to emitter voltage	V <sub>CEO</sub>	$I_{\rm C} = 2 {\rm mA}, I_{\rm B} = 0$	50	1	<b>2</b> E	V
Callester and ff annual	I <sub>CBO</sub>	$V_{CB} = 50V, I_E = 0$	60		0.1	μΑ
Collector cutoff current	I <sub>CEO</sub>	$V_{CE} = 50V, I_B = 0$	LE		0.5	μA
Emitter cutoff current	I <sub>EBO</sub>	$V_{EB} = 6V, I_C = 0$			0.01	mA
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = 10V, I_{C} = 5mA$	160		460	
Forward current transfer h <sub>FE</sub> ratio	h <sub>FE</sub> (small/large)*	$V_{CE} = 10V, I_{C} = 5mA$	0.5	0.99		
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0.3 {\rm mA}$			0.25	V
Output voltage high level	V <sub>OH</sub>	$V_{CC} = 5V, V_B = 0.5V, R_L = 1k\Omega$	4.9			V
Output voltage low level	V <sub>OL</sub>	$V_{CC} = 5V$ , $V_B = 2.5V$ , $R_L = 1k\Omega$			0.2	V
Transition frequency	f <sub>T</sub>	$V_{CB} = 10V, I_E = -2mA, f = 200MHz$		150		MHz
Input resistance	R <sub>1</sub>		-30%	10	+30%	kΩ

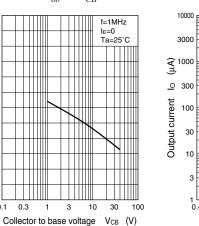
\* Ratio between 2 elements

# **Composite Transistors**





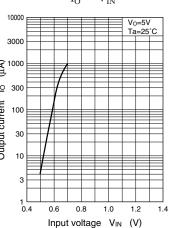




2

0 └ 0.1





Vo=0.2V Ta=25°C 

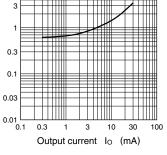
V<sub>IN</sub> — I<sub>O</sub>

100

30

10 Ξ

Input voltage Vin



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